NPN SILICON HIGH FREQUENCY TRANSISTOR

UPA801TC

FEATURES

- SMALL PACKAGE OUTLINE: 1.5 mm x 1.1 mm, 33% smaller than conventional SOT-363 package
- LOW HEIGHT PROFILE Just 0.55 mm high

NEC

- FLAT LEAD STYLE: Reduced lead inductance improves electrical performance
- HIGH COLLECTOR CURRENT: IC MAX = 100 mA

ABSOLUTE MAXIMUM RATINGS¹ (TA = 25°C)

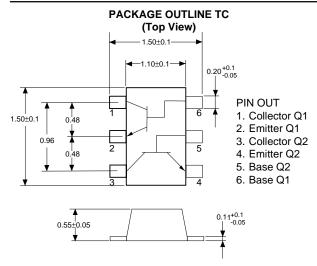
SYMBOLS	PARAMETERS	UNITS	RATINGS
Vсво	Collector to Base Voltage	V	20
Vceo	Collector to Emitter Voltage	V	12
Vebo	Emitter to Base Voltage	V	3
lc	Collector Current	mA	100
PT	Total Power Dissipation 1 Die 2 Die	mW mW	TBD TBD
TJ	Junction Temperature	°C	150
Тѕтс	Storage Temperature	°C	-65 to +150

Note: 1. Operation in excess of any one of these parameters may result in permanent damage.

DESCRIPTION

The UPA801TC contains two NE856 NPN high frequency silicon bipolar chips. NEC's new ultra small TC package is ideal for all portable wireless applications where reducing board space is a prime consideration. Each transistor chip is independently mounted and easily configured for two stage cascode LNAs and other applications.

OUTLINE DIMENSIONS (Units in mm)



ELECTRICAL CHARACTERISTICS (TA = 25°C)

PART NUMBER PACKAGE OUTLINE			UPA801TC TC			
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX	
Ісво	Collector Cutoff Current at VcB = 10 V, IE = 0	μA			1.0	
Іево	Emitter Cutoff Current at VEB = 1 V, IC = 0	μA			1.0	
hfe	Forward Current Gain ¹ at VcE = 3 V, Ic = 7 mA		70	120	250	
fт	Gain Bandwidth at VCE = 3 V, IC = 7 mA	GHz	3.0	4.5		
Cre	Feedback Capacitance ² at VcB = 3 V, IE = 0, f = 1 MHz	pF		0.7	1.5	
S21E ²	Insertion Power Gain at VcE = 3 V, Ic = 7 mA, f = 1 GHz	dB	7	9		
NF	Noise Figure at Vce = 3 V, Ic = 7 mA, f = 1 GHz	dB		1.2	2.5	

Notes: 1.Pulsed measurement, pulse width \leq 350 µs, duty cycle \leq 2 %.

2. The emitter terminal should be connected to the ground terminal of the 3 terminal capacitance bridge.

For Tape and Reel version use part number UPA801TC-T1, 3K per reel.

California Eastern Laboratories

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